Growth rate of ALD Al_2O_3 on nanocellulose – quantification technique and analysis

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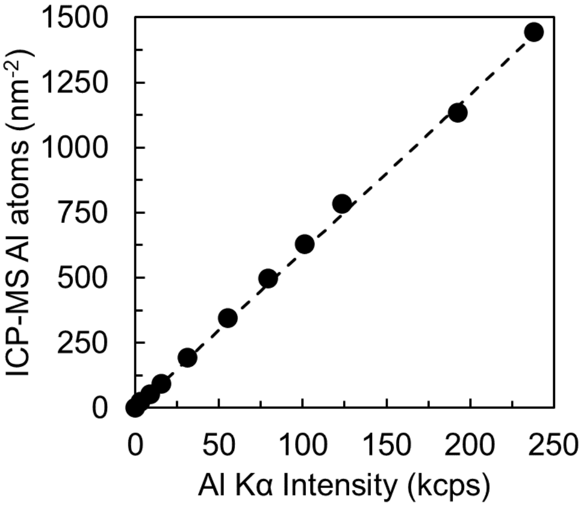

Figure 1: Calibration curve between ICP-MS and XRF for the quantification of ALD Al_2O_3 samples deposited on nanocellulose substrates.

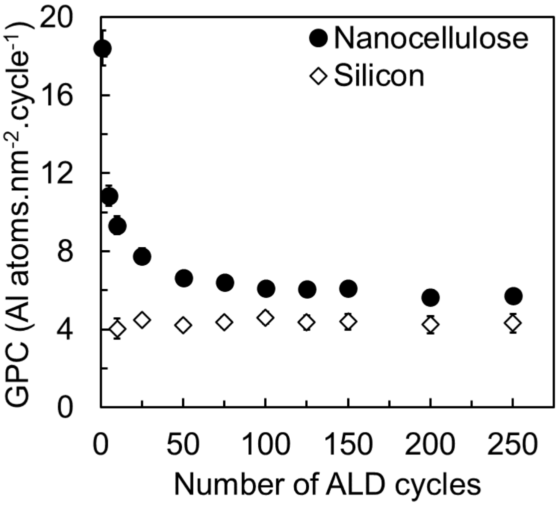

Figure 2: The atomic GPC, as a function of the number of ALD cycles for ALD-Al_2O_3 samples deposited on nanocellulose and silicon substrates at 250°C.